

## Efficient Absorption of Cu<sub>2</sub>WX<sub>4</sub> (X = S, Se, Te) for Photovoltaic Application: A Theoretical Study

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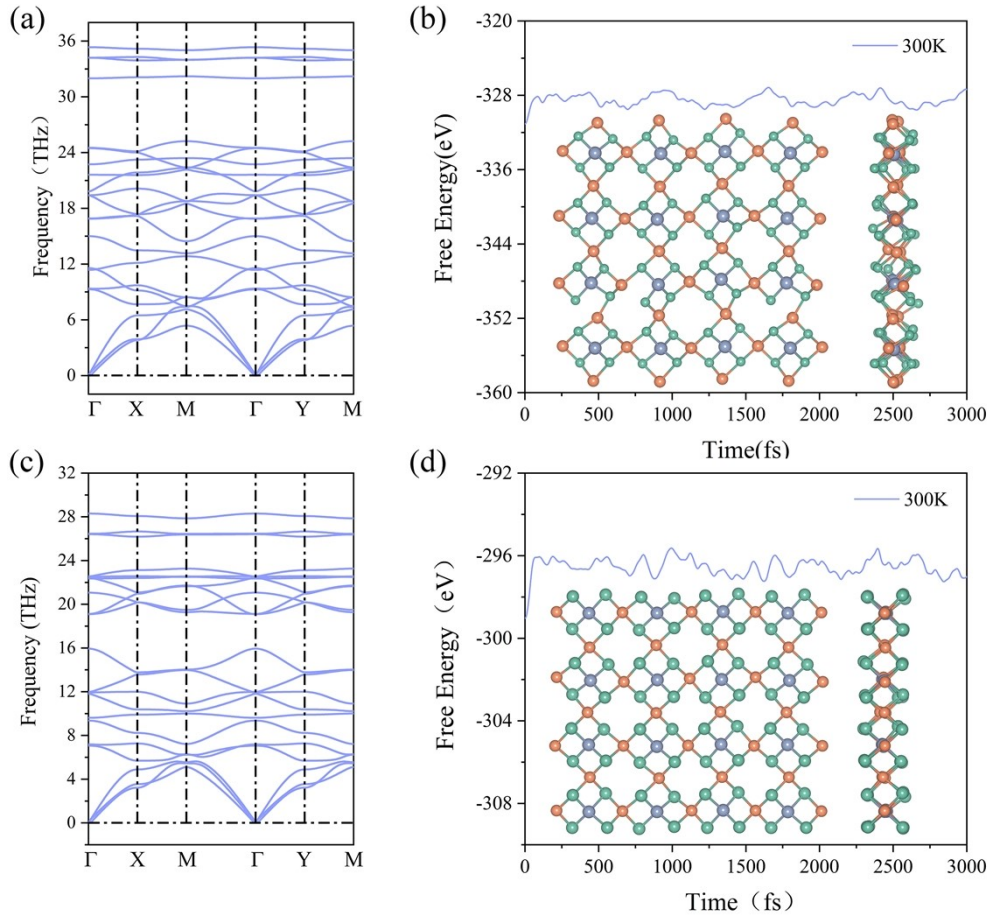
### Computational methods

According to the DP theory, the 2D carrier mobility  $\mu$  can be described by the following equation:<sup>1</sup>

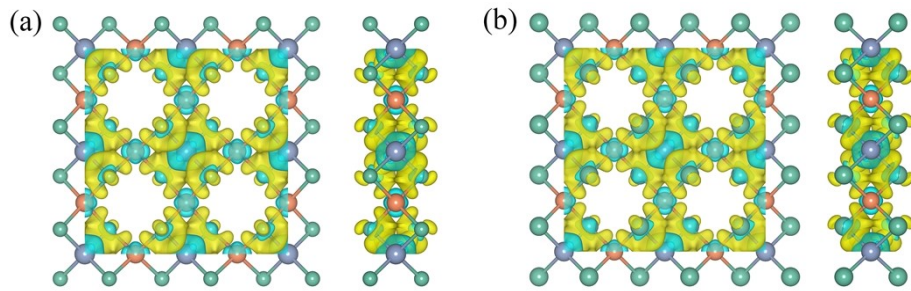
$$\mu = \frac{e\hbar^3 C}{3k_B T |m_{e/h}^*|^2 (E_d)^2}$$

where  $e$ ,  $\hbar$ ,  $k_B$ , and  $T$  are the electron charge, the reduced Planck constant, the Boltzmann constant, and the temperature, respectively.  $C$  is the elastic modulus and

$E_d$  is the deformation potential.  $m_{e/h}^* = \pm \hbar^2 \left( \frac{d^2 E_k}{dk^2} \right)^{-1}$  is the effective mass.



**Fig. S1** (a) Phonon spectrum and (b) variation of total energy of the  $\text{Cu}_2\text{WSe}_4$  monolayer. (c) Phonon spectrum and (d) variation of total energy of the  $\text{Cu}_2\text{WTe}_4$  monolayer. The insets in (b) and (d) are top and side views of the snapshot at the end of simulation of  $\text{Cu}_2\text{WSe}_4$  and  $\text{Cu}_2\text{WTe}_4$ , respectively.



**Fig. S2** The calculated charge density difference of (a)  $\text{Cu}_2\text{WSe}_4$  and (b)  $\text{Cu}_2\text{WTe}_4$ . The isosurface value is set to  $0.06 \text{ e}\text{\AA}^{-3}$ . The cyan and yellow regions represent electron depletion and accumulation, respectively.

## Reference

- 1 J. Bardeen and W. Shockley, *Phys. Rev.*, 1950, **80(1)**, 72.